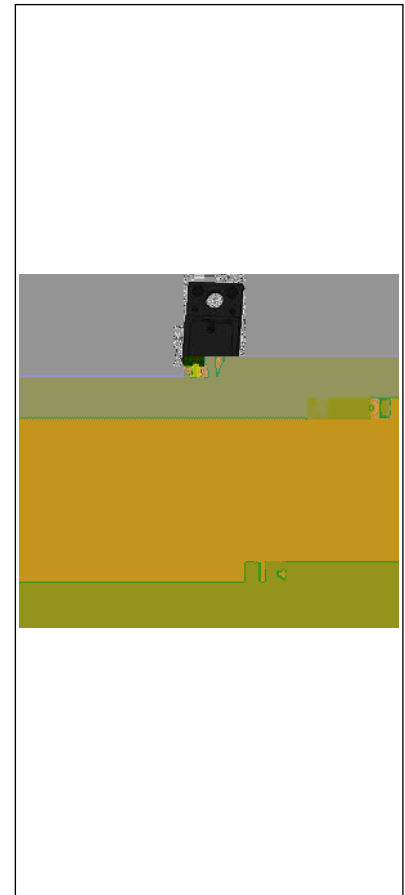




The JST08F-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST08F-800SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. By using an external plastic package, JST08F-800SW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT} / /$	10/10/10	mA

Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c = 94^\circ C$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$ , $T_j=25^\circ C$ )	$I_{TSM}$	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$ , $T_j=25^\circ C$ )		88	
$I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^\circ C$ )	$I^2t$	32	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 I_{GT}$ , $f=100Hz$ , $T_j=125^\circ C$ )	$di/dt$	50	$A/\mu s$



Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.5	kV

( $T_j=25$  unless otherwise specified)

$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
$I_H$	$I_T=100mA$		MAX.	15	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=125$		MIN.	400	V/ $\mu s$
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$ , $T_j=125$		MIN.	3	A/ms
$t_{on}$	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	$\mu s$
$t_{off}$				25	

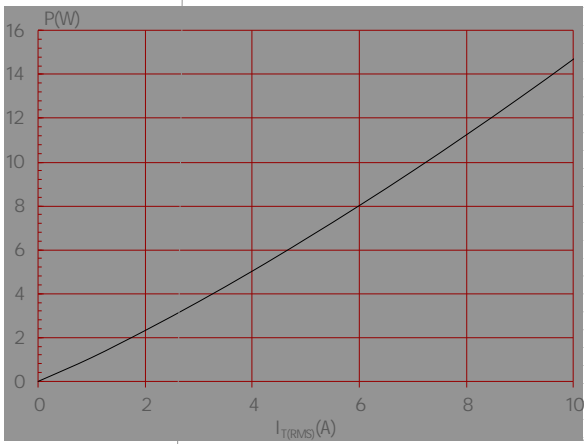
$V_{TM}$	$I_{TM}=11A$ $t_p=380\mu s$	$T_j=25$		1.5	V
$V_{TO}$	Threshold voltage	$T_j=125$		0.8	V
$R_D$	Dynamic resistance	$T_j=125$		44	m
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$		5	$\mu A$
$I_{RRM}$		$T_j=125$		0.5	mA

$R_{th(j-c)}$	junction to case (AC)			2.8	/W
$R_{th(j-a)}$	junction to ambient (AC)			60	/W





Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

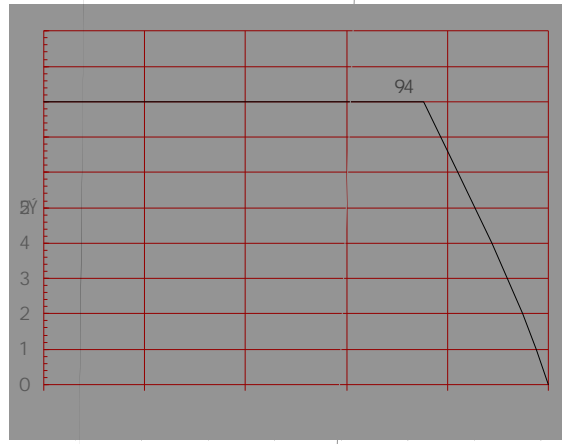




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

